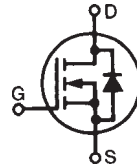


**GigaMOS™ Trench  
HiperFET™  
Power MOSFET**

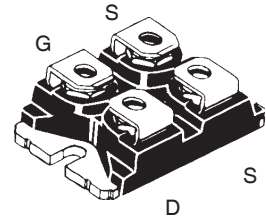
**IXFN360N10T**



N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Rectifier

$V_{DSS} = 100V$   
 $I_{D25} = 360A$   
 $R_{DS(on)} \leq 2.6m\Omega$   
 $t_{rr} \leq 130ns$

miniBLOC, SOT-227  
 E153432



G = Gate      D = Drain  
S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source ( Gate Return ) Terminal.

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $175^\circ C$	100	V
$V_{DGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GS} = 1M\Omega$	100	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$ (Chip Capability)	360	A
$I_{LRMS}$	Lead Current Limit, RMS	200	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	900	A
$I_A$	$T_C = 25^\circ C$	100	A
$E_{AS}$	$T_C = 25^\circ C$	3	J
$P_D$	$T_C = 25^\circ C$	830	W
$dV/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 175^\circ C$	20	V/ns
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ Minute	2500	V~
	$I_{ISOL} \leq 1mA$ $t = 1$ Second	3000	V~
$M_d$	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
<b>Weight</b>		30	g

**Features**

- International Standard Package
- $175^\circ C$  Operating Temperature
- High Current Handling Capability
- Avalanche Rated
- Fast Intrinsic Rectifier
- Low  $R_{DS(on)}$

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ .	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 3mA$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 150^\circ C$			25 $\mu A$ 2.5 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 100A$ , Note 1			2.6 $m\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1	110	180	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		33	nF
$C_{oss}$			3160	pF
$C_{rss}$			400	pF
$R_{Gi}$	Gate Input Resistance		1.20	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 100\text{A}$ $R_G = 1\Omega$ (External)		47	ns
$t_r$			100	ns
$t_{d(off)}$			80	ns
$t_f$			160	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		525	nC
$Q_{gs}$			145	nC
$Q_{gd}$			165	nC
$R_{thJC}$			0.05	$^\circ\text{C/W}$
$R_{thCS}$				

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_s$	$V_{GS} = 0\text{V}$			360 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			1440 A
$V_{SD}$	$I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			1.2 V
$t_{rr}$	$I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 50\text{V}$			130 ns
$I_{RM}$			6.60	A
$Q_{RM}$			0.33	$\mu\text{C}$

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### SOT-227B (IXFN) Outline



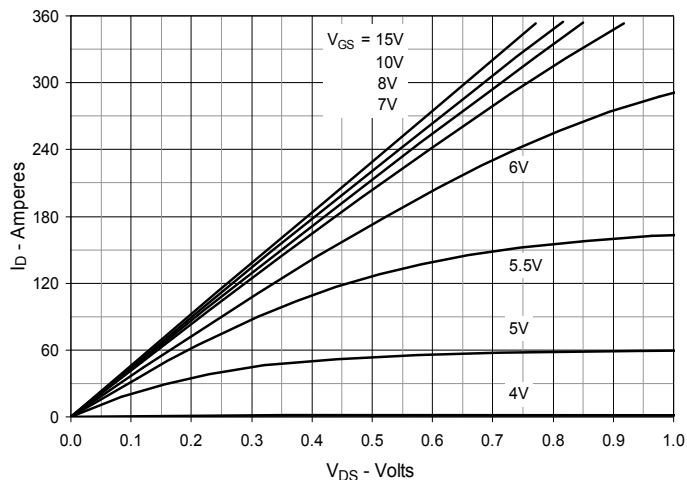
(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

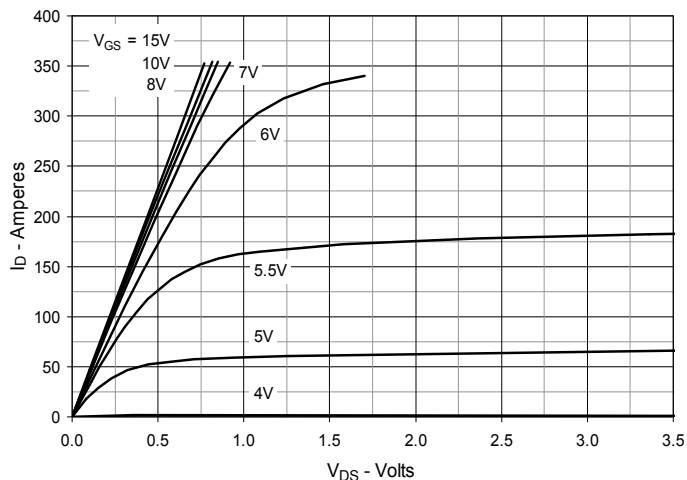
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

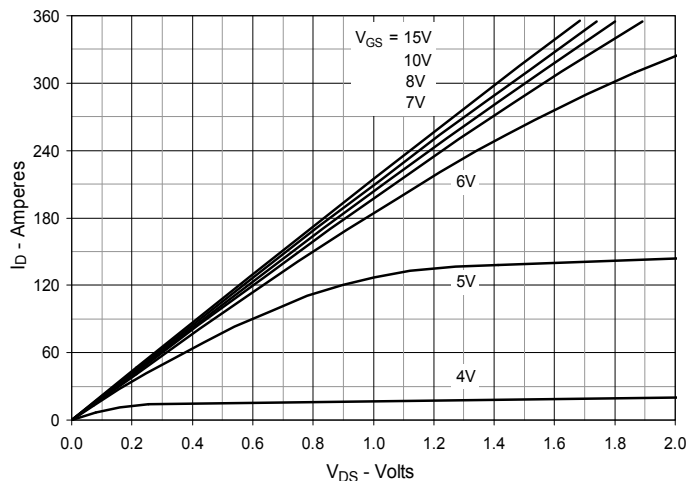
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



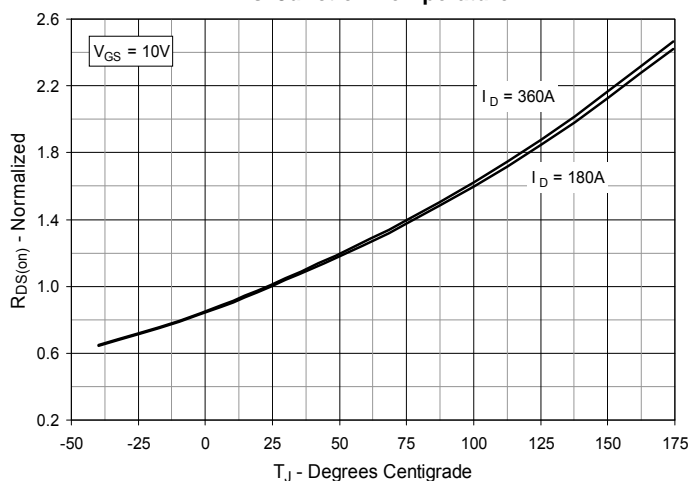
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



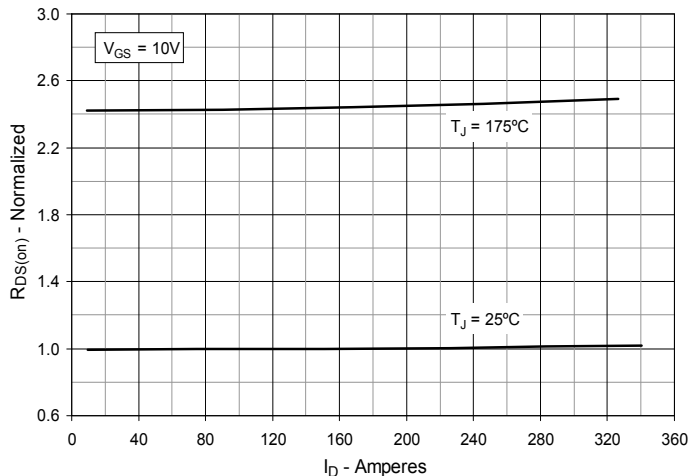
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



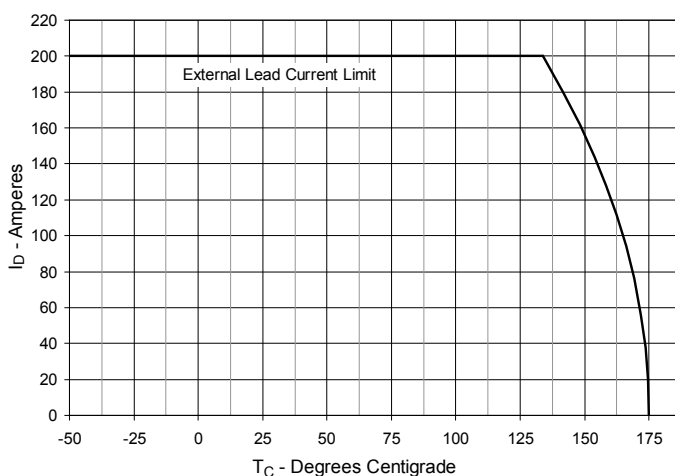
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 180\text{A}$  Value vs. Junction Temperature**



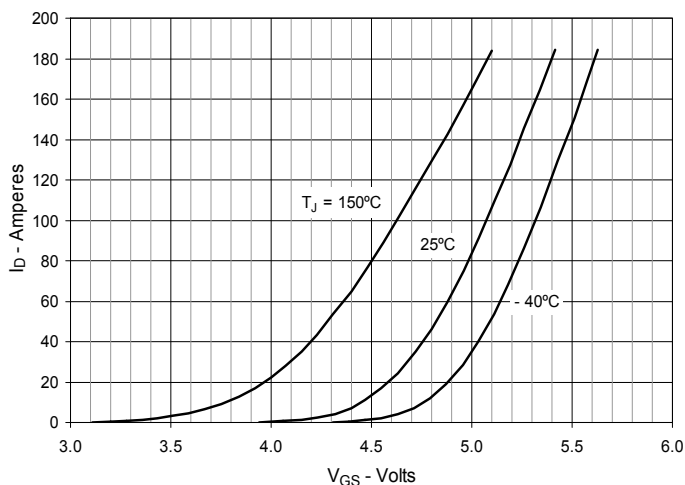
**Fig. 5. Normalized  $R_{DS(on)}$  vs. Drain Current**



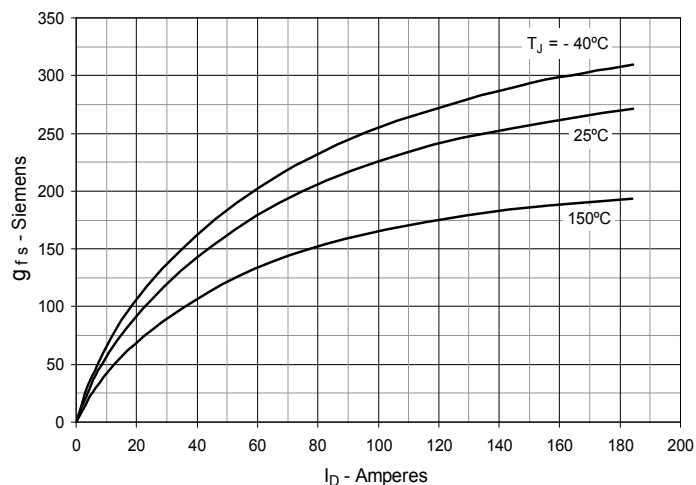
**Fig. 6. Drain Current vs. Case Temperature**



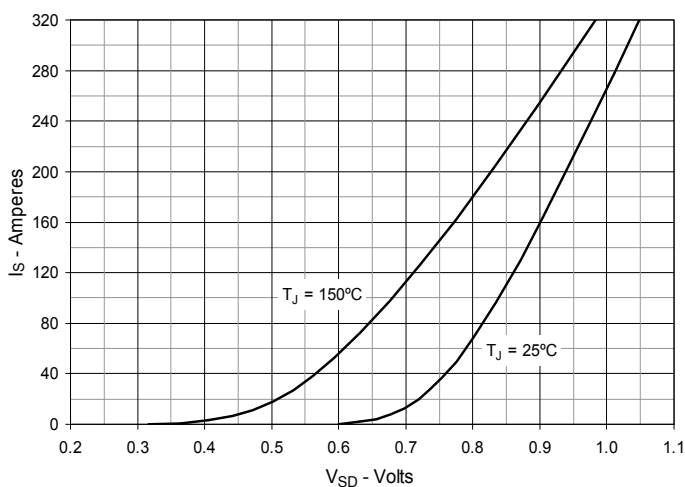
**Fig. 7. Input Admittance**



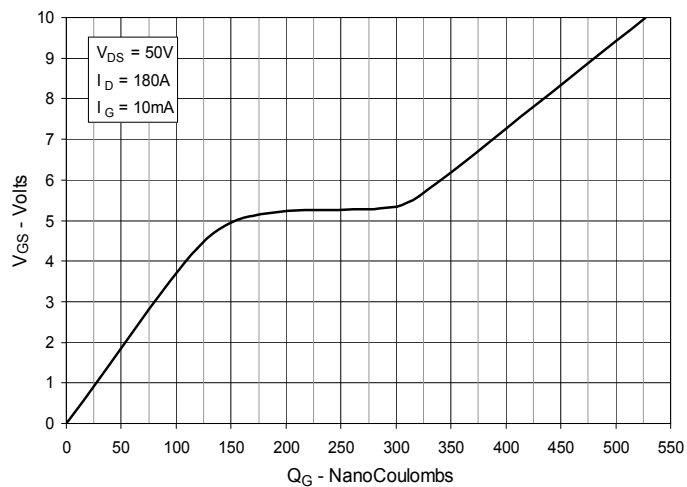
**Fig. 8. Transconductance**



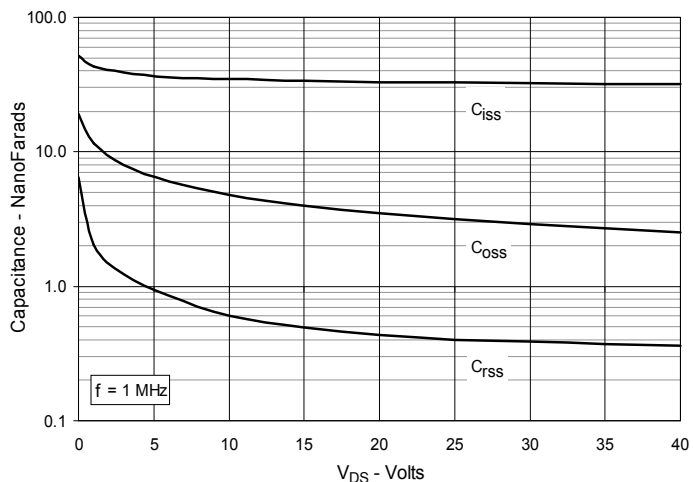
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



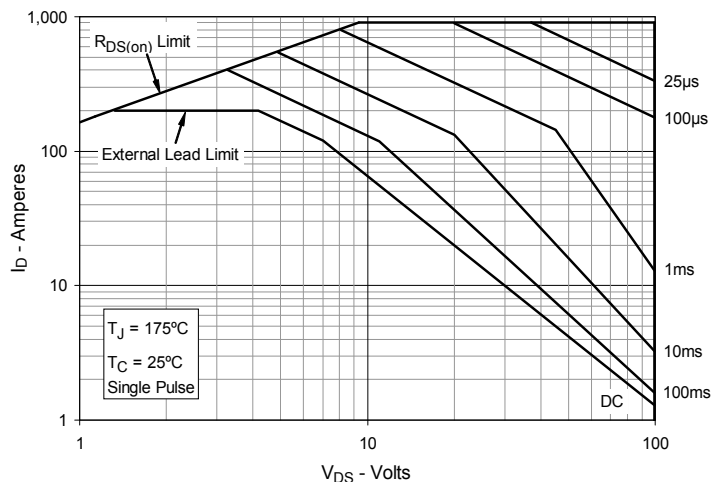
**Fig. 10. Gate Charge**



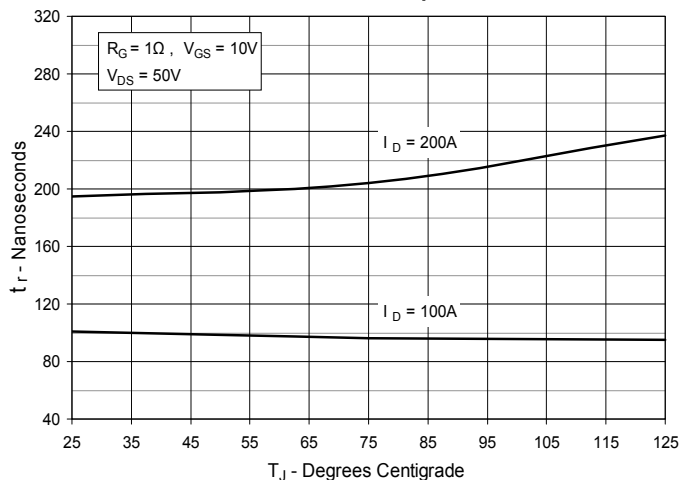
**Fig. 11. Capacitance**



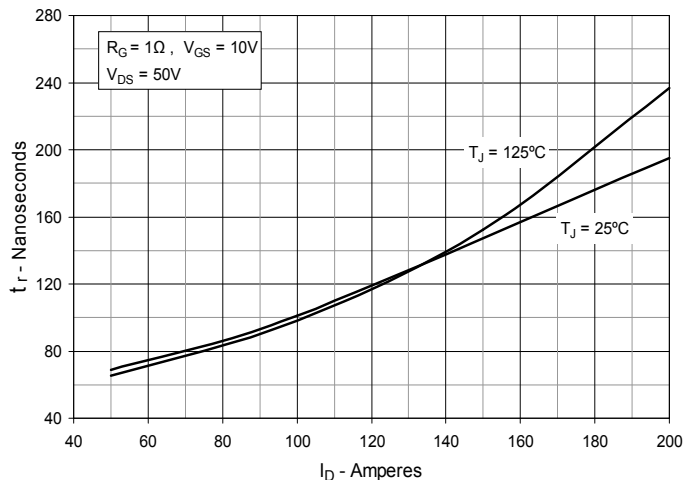
**Fig. 12. Forward-Bias Safe Operating Area**



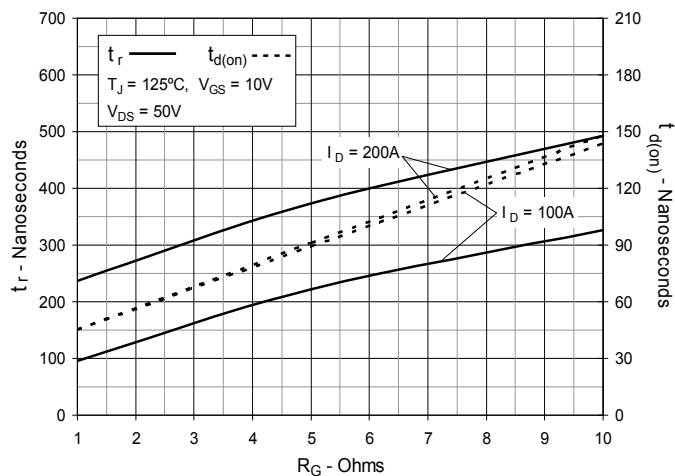
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



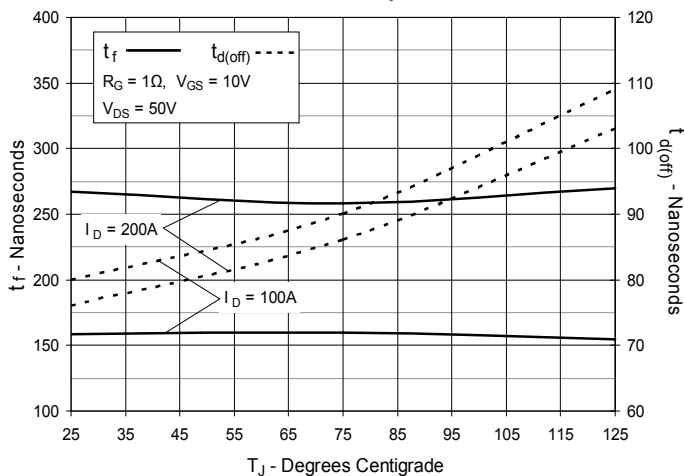
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



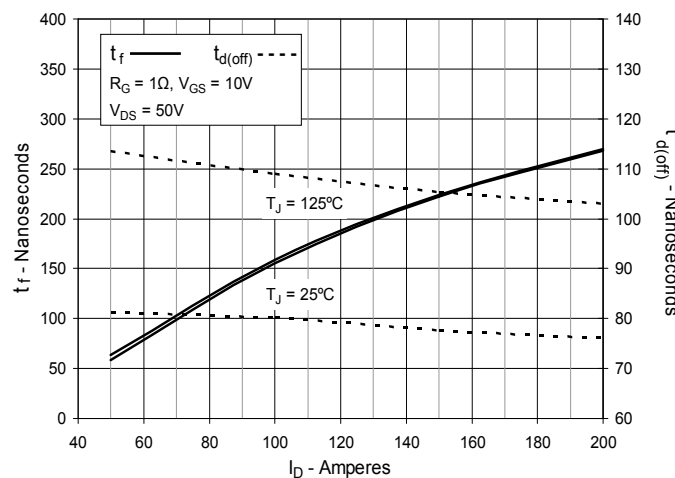
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

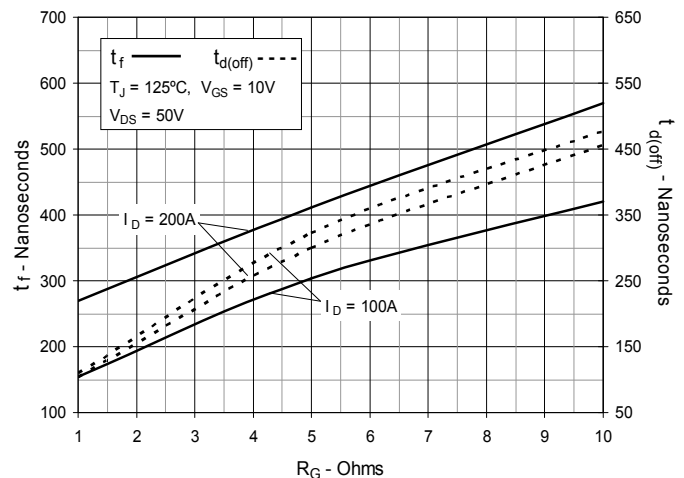


Fig. 19. Maximum Transient Thermal Impedance

